

100V PNP MEDIUM POWER TRANSISTOR IN SOT223

Features

- BV_{CEO} > -100V
- $BV_{ECO} > -7V$
- I_C = -2A High Continuous Current
- Low Saturation Voltage V_{CE(sat)} < -130mV @ -1A
- $R_{CE(sat)} = 100 m\Omega$
- Complementary NPN Type: ZXTN19100CG
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.112 grams (Approximate)

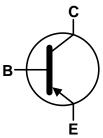
Applications

- Motor Drive
- High Side Driver

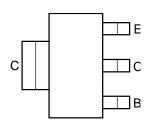




Top View



Device Symbol



Top View Pin-Out

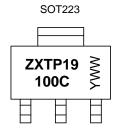
Ordering Information (Note 4)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTP19100CGTA	AEC-Q101	ZXTP19100C	7	12	1.000

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + CI) and <1000ppm antimony compounds.</p>
 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



ZXTP19100C = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 5= 2015) WW or $\overline{W}W = \text{Week Code } (01~53)$



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-110	V
Collector-Emitter Voltage (forward blocking)	V _{CEX}	-110	V
Collector-Emitter Voltage	V _{CEO}	-100	V
Emitter-Collector Voltage (reverse blocking)	V _{ECO}	-7	V
Emitter-Base Voltage	V _{EBO}	-7	V
Continuous Collector Current	Ic	-2	А
Base Current	I _B	-1	А
Peak Pulse Current	Ісм	-3	Α

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 5)		1.2 9.6		
Power Dissipation	(Note 6)		1.6 12.8	W mW/°C	
Linear Derating Factor	(Note 7)	P _D	3 24		
	(Note 8)		5.3 42		
	(Note 5)		104		
Thermal Decistores Junction to Ambient	(Note 6)		78		
Thermal Resistance, Junction to Ambient	(Note 7)	R _{θJA}	42	°C/W	
	(Note 8)		23.5		
Thermal Resistance, Junction to Lead (Note 9)		$R_{ heta JL}$	16		
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C		

ESD Ratings (Note 10)

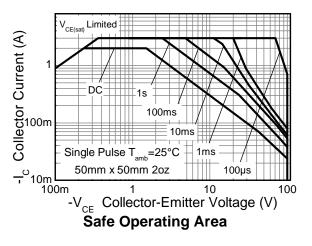
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

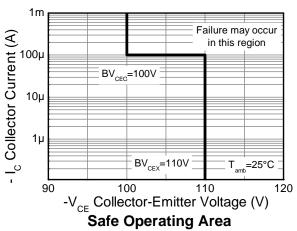
Notes:

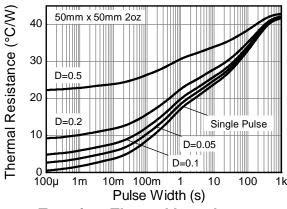
- 5. For a device mounted with the collector lead on 15mm x 15mm 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady-state.
- 6. Same as Note 6, except the device is mounted on 25mm x 25mm 1oz copper.
- 7. Same as Note 6, except the device is mounted on 50mm x 50mm 2oz copper.
- 8. Same as Note 8 measured at t<5 seconds.
- 9. Thermal resistance from junction to solder-point (at the end of the collector lead).
- 10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

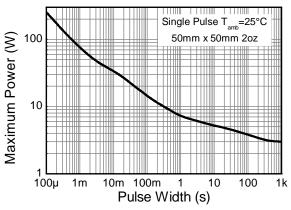


Thermal Characteristics and Derating Information (@TA = +25°C, unless otherwise specified.)



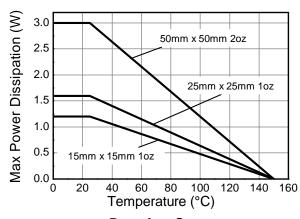






Transient Thermal Impedance

Pulse Power Dissipation



Derating Curve



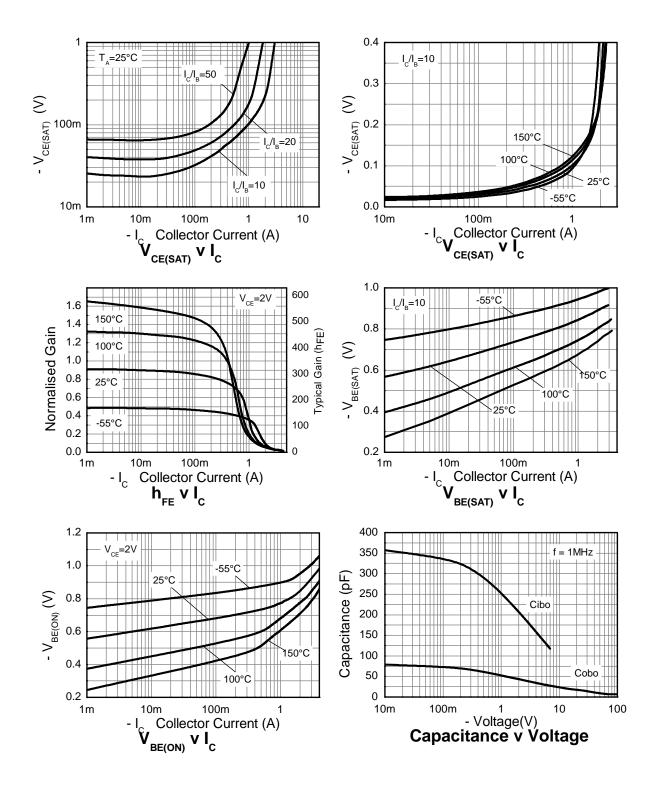
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-110	-135	-	V	$I_{C} = -100 \mu A$
Collector-Emitter Breakdown Voltage (Note 11)	BV _{CEO}	-100	-135	-	V	I _C = -10mA
Collector-Base Breakdown Voltage (forward blocking)	BV_CEX	-110	-130			I _C = -100μA
Emitter-Collector Breakdown Voltage (reverse blocking)	BV _{ECX}	-7	-8.3	_	V	$I_C = -100\mu A$, $R_{BC} < 1k\Omega$ or $0.25V < V_{BC} > -0.25V$
Emitter-Collector Breakdown Voltage (reverse blocking)	BV _{ECO}	-7	-8.7	-	٧	I _E = -100μA
Emitter-Base Breakdown Voltage	BV_EBO	-7	-8.3	-	٧	$I_E = -100 \mu A$
Collector Cut-Off Current	1	_	< 1	-50	nA	V _{CB} = -110V
Collector Cut-Oil Current	I _{CBO}	_	-	-0.5	μΑ	$V_{CB} = -110V, T_A = +100$ °C
Emitter Cut-Off Current	I _{EBO}	_	< 1	-50	nA	$V_{EB} = -5.6V$
		_	-100	-130	mV	$I_C = -500 \text{mA}, I_B = -20 \text{mA}$
Collector-Emitter Saturation Voltage (Note 11)	V _{CE(sat)}	_	-100	-125	mV	$I_C = -1A$, $I_B = -100mA$
Collector-Entitler Saturation voltage (Note 11)		_	-180	-230	mV	$I_C = -1A$, $I_B = -50mA$
		_	-220	-295	mV	$I_C = -2A$, $I_B = -200mA$
Base-Emitter Saturation Voltage (Note 11)	V _{BE(sat)}	_	-890	-1,000	mV	$I_C = -2A$, $I_B = -200mA$
Base-Emitter Turn-On Voltage (Note 11)	$V_{BE(on)}$	_	-840	-950	mV	$I_C = -2A$, $V_{CE} = -2V$
		200	300	500		$I_C = -100 \text{mA}, V_{CE} = -2 \text{V}$
DC Current Gain (Note 11)	h _{FE}	70	130	-	Ī	$I_C = -1A$, $V_{CE} = -2V$
		20	28	-	I	$I_C = -2A$, $V_{CE} = -2V$
Current Gain-Bandwidth Product (Note 11)	f⊤	-	142	_	MHz	$V_{CE} = -10V, I_{C} = -100mA,$ f = 50MHz
Input Capacitance (Note 11)	C _{ibo}	_	291	400	pF	$V_{EB} = -0.5V$, $f = 1MHz$
Output Capacitance (Note 11)	C _{obo}	_	23.5	40	pF	V _{CB} = -10V, f = 1MHz
Delay Time	t _d	_	24.7		ns	1 500 - 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1
Rise Time	t _r	_	22.4	_	ns	$I_{C} = -500 \text{mA}, V_{CC} = -10 \text{V},$
Storage Time	t _s	_	660		ns	$I_{B1} = -I_{B2} = -50 \text{mA}$ $R_b = 100 \text{W}, R_c = 20 \text{W}$
Fall Time	t _f	_	107	-	ns	ND - 1000V, NC = 20VV

Note: 11. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



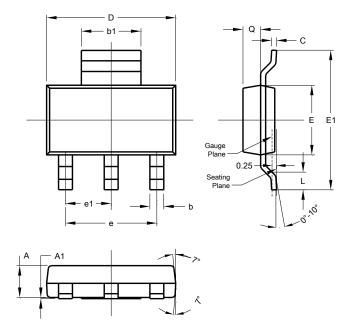
Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)





Package Outline Dimensions

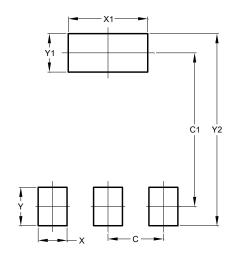
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223						
Dim	Min	Max	Тур			
Α	1.55	1.65	1.60			
A1	0.010	0.15	0.05			
b	0.60	0.80	0.70			
b1	2.90	3.10	3.00			
С	0.20	0.30	0.25			
D	6.45	6.55	6.50			
Е	3.45	3.55	3.50			
E1	6.90	7.10	7.00			
е	-	-	4.60			
e1	-	-	2.30			
L	0.85	1.05	0.95			
Q	0.84	0.94	0.89			
All Dimensions in mm						

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
С	2.30		
C1	6.40		
X	1.20		
X1	3.30		
Y	1.60		
Y1	1.60		
Y2	8.00		



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